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(54) Title: MAKING SEMICONDUCTOR BODIES FROM MOLTEN MATERIAL USING A FREE-STANDING INTERPOSER SHEET

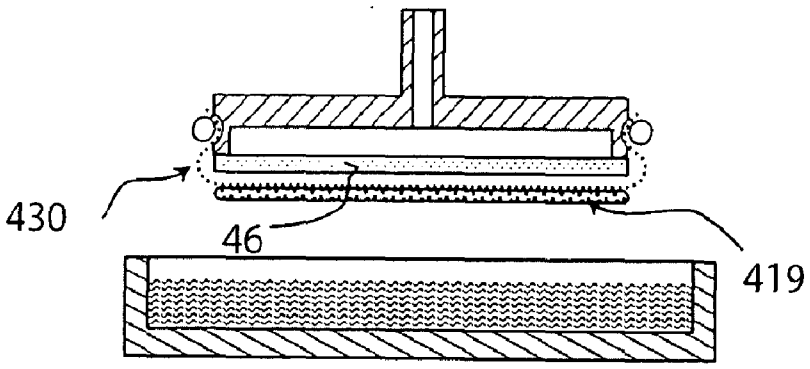


Fig. 4G

(57) Abstract: Interposer sheet for making silicon solar semiconductor bodies. Interposer is free-standing, thin, flexible, porous and withstands chemical/thermal environment of molten semiconductor without degradation. Interposer is of ceramic material, such as silica, silicon nitride, silicon oxynitride, silicon oxycarbide, silicon carbide, silicon carbonitride, silicon oxycarbonitride and others. Provided between a forming surface of a mold sheet, and the molten material from which a semiconductor body will be formed. Secured to the forming surface or deposited upon the melt. Interposer suppresses grain nucleation, and limits heat flow from the melt, promotes separation of the semiconductor body from the forming surface, prefabricated before use. Because free-standing and not adhered to the forming surface, problems of mismatch of CTE are minimized. Interposer and semiconductor body are free to expand and contract relatively independently of the forming surface.

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